

Notice of References Cited	Application/Control No. 10/580,625		Applicant(s)/Patent Under Reexamination HUETING ET AL.	
	Examiner Hsin-Yi (Steven) Hsieh		Art Unit 2811	Page 1 of 1

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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